Notice of Allowability	Applicati n No.	857,453 KING ET AL.	
	09/857,453 Examiner		
	Lamino		
	Victor A Mandala Jr.	2826	
The MAILING DATE of this communication app All claims being allowable, PROSECUTION ON THE MERITS Is herewith (or previously mailed), a Notice of Allowance (PTOL-88 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT of the Office or upon petition by the applicant. See 37 CFR 1.37	S (OR REMAINS) CLOSED in 5) or other appropriate commun RIGHTS. This application is su	this application. If not includation will be mailed in due	ded e course. THIS
1. This communication is responsive to <u>Amendment C filed</u>	<u>10/16/03</u> .		
2. The allowed claim(s) is/are <u>21-23 and 26-32</u> .	<u>.</u>	12 11 / 19 1	
3. The drawings filed on <u>04 June 2001</u> are accepted by the			F TOORS HOW
 4. Acknowledgment is made of a claim for foreign priority (a) All b) Some* c) None of the: 	under 35 U.S.C. § 119(a)-(d) o	(t).	The second second of the second second of the second secon
1. Certified copies of the priority documents ha	ve heen received		,
2. Certified copies of the priority documents ha		ı No.	
3. \(\sum \) Copies of the certified copies of the priority documents have been received in this national stage application from the			
International Bureau (PCT Rule 17.2(a)).		0.411	
* Certified copies not received:			
5. Acknowledgment is made of a claim for domestic priority reference was included in the first sentence of the specific			e a specific
(a) The translation of the foreign language provisional	• •		
6. Acknowledgment is made of a claim for domestic priority in the first sentence of the specification or in an Application		121 since a specific referer	nce was included
Applicant has THREE MONTHS FROM THE "MAILING DATE" below. Failure to timely comply will result in ABANDONMENT of			
7. A SUBSTITUTE OATH OR DECLARATION must be sub- INFORMAL PATENT APPLICATION (PTO-152) which gi			NOTICE OF
8. \square CORRECTED DRAWINGS (as "replacement sheets") mi			
(a) ☐ including changes required by the Notice of Draftspe	rson's Patent Drawing Review	(PTO-948) attached	
1) hereto or 2) to Paper No			
(b) ☐ including changes required by the proposed drawing correction filed, which has been approved by the Examiner.			
(c) including changes required by the attached Examine	r's Amendment / Comment or i	n the Office action of Paper	No
Identifying indicia such as the application number (see 37 CFR each sheet. Replacement sheet(s) should be labeled as such in			e back) of
9. DEPOSIT OF and/or INFORMATION about the departached Examiner's comment regarding REQUIREMENT FOR			Note the
Attachm nt(s)			
1⊠ Notice of References Cited (PTO-892)		mal Patent Application (PTC	•
2 Notice of Draftperson's Patent Drawing Review (PTO-948)		mary (PTO-413), Paper No	
3 Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No	^{)8),} 7⊠ Examiner's Ar	nendment/Comment	
4 Examiner's Comment Regarding Requirement for Deposit of Biological Material	8⊠ Examiner's St 9∏ Other .	atement of Reasons for Allo	wance

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U.S. Patent and Trademark Office

DETAILED ACTION

Examiner's Amendment

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

1. The examiner amends the specification by the addition of an abstract as written below:

Abstract

A semiconductor device including a gate oxide of multiple thicknesses for multiple transistors where the gate oxide thicknesses are altered through the growth process of implanted oxygen ions into selected regions of a substrate. The implanted oxygen ions accelerate the growth of the oxide which also allow superior quality and reliability of the oxide layer, where the quality is especially important, compared to inter-metal dielectric layers. A technique has been used to vary the thickness of an oxide layer grown on a silicon wafer during oxidation growth process by implanting nitrogen into selected regions of the substrate, which the nitrogen ions retard the growth of the silicon oxide resulting in a diminished oxide quality. Therefore it is desirable to fabricate a semiconductor device with multiple thicknesses of gate oxide by the implanted oxygen ion technique.

Application/Control Number: 09/857,453

Art Unit: 2826

Allowable Subject Matter

The following is an examiner's statement of reasons for allowance:

2. The Applicant has argued the allowability of claims 21-23 and 26-32 in Amendment C

filed on 9/08/03. The Applicant discusses that the divisional, #09/449063, of this application has

gone to Appeal on very similar claims to claims 21-23 and 26-32 of this application, which the

rejections in Application #09/449063 where also very similar to the rejections at hand, and the

Board of Appeals has reversed the rejections in Application #09/449063. The examiner has

considered the Applicant's arguments and finds them to be persuasive.

3. Claims 21-23 & 26-32 are allowed.

Any comments considered necessary by applicant must be submitted no later than the

payment of the issue fee and, to avoid processing delays, should preferably accompany the issue

fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for

Allowance."

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Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Victor A Mandala Jr. whose telephone number is (703) 308-6560. The examiner can normally be reached on Monday through Thursday from 8am till 6pm..

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on (703) 308-6601. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9318.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

VAMJ 1/22/04